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FIG. 1A

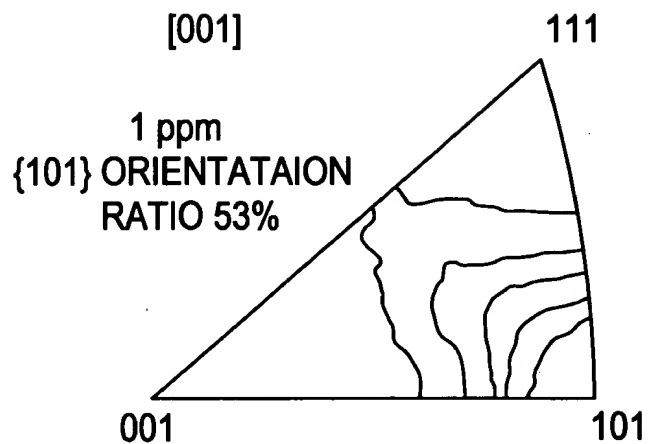


FIG. 1B

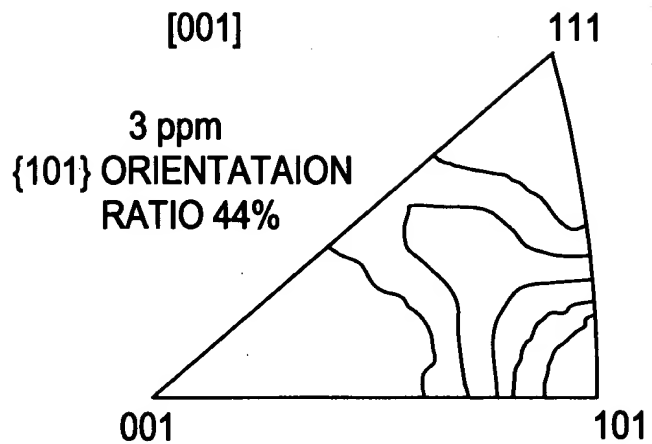


FIG. 1C

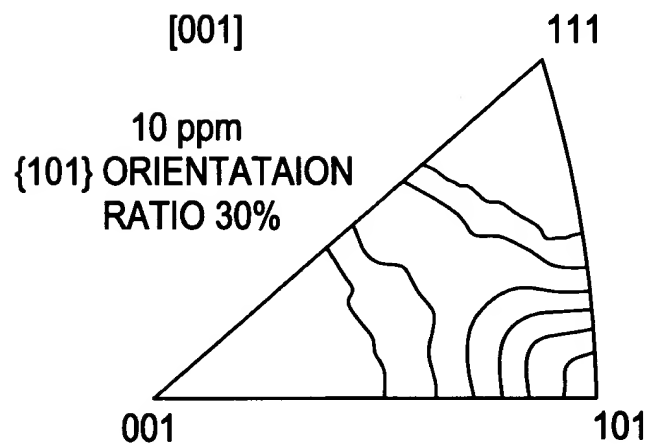
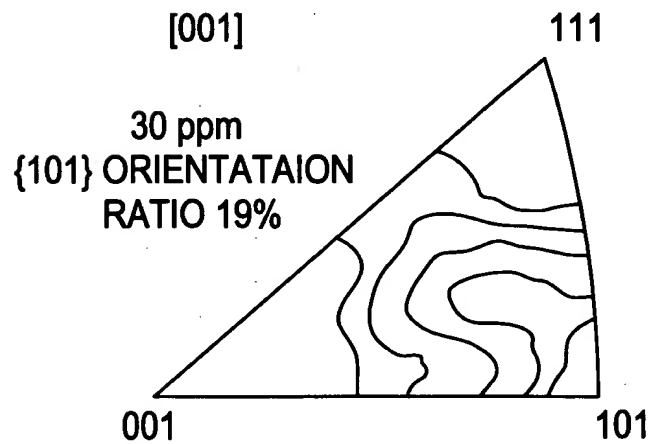


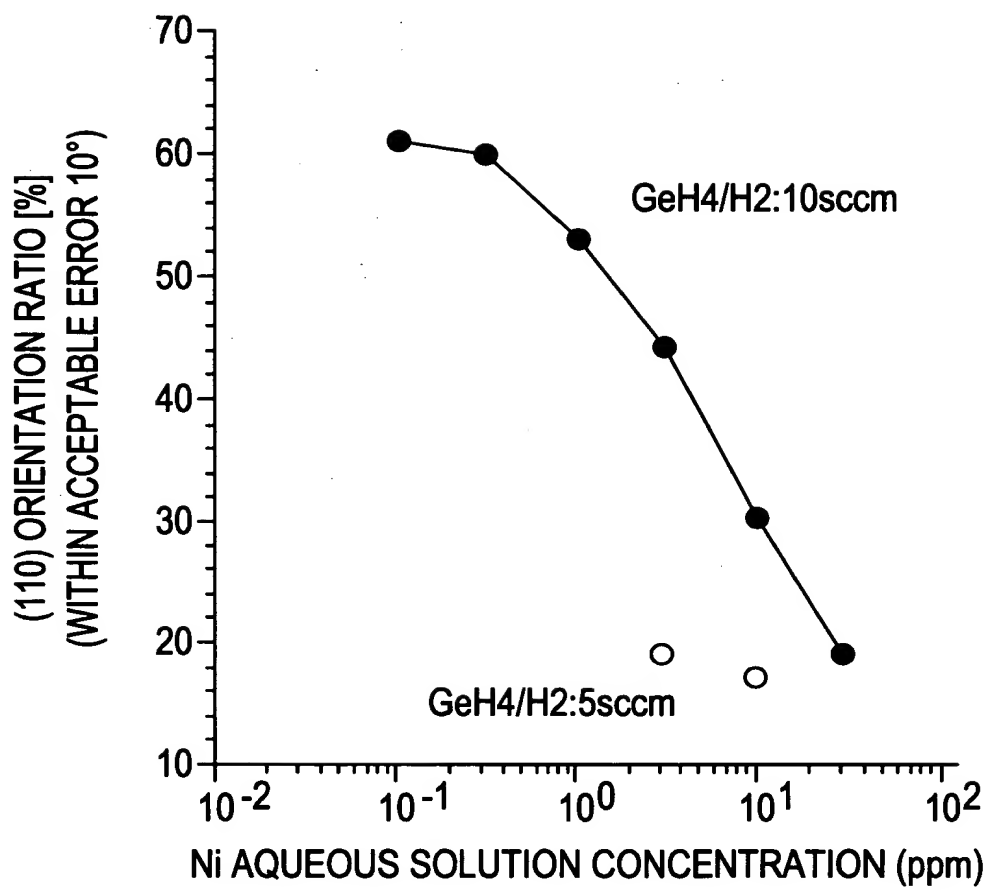
FIG. 1D





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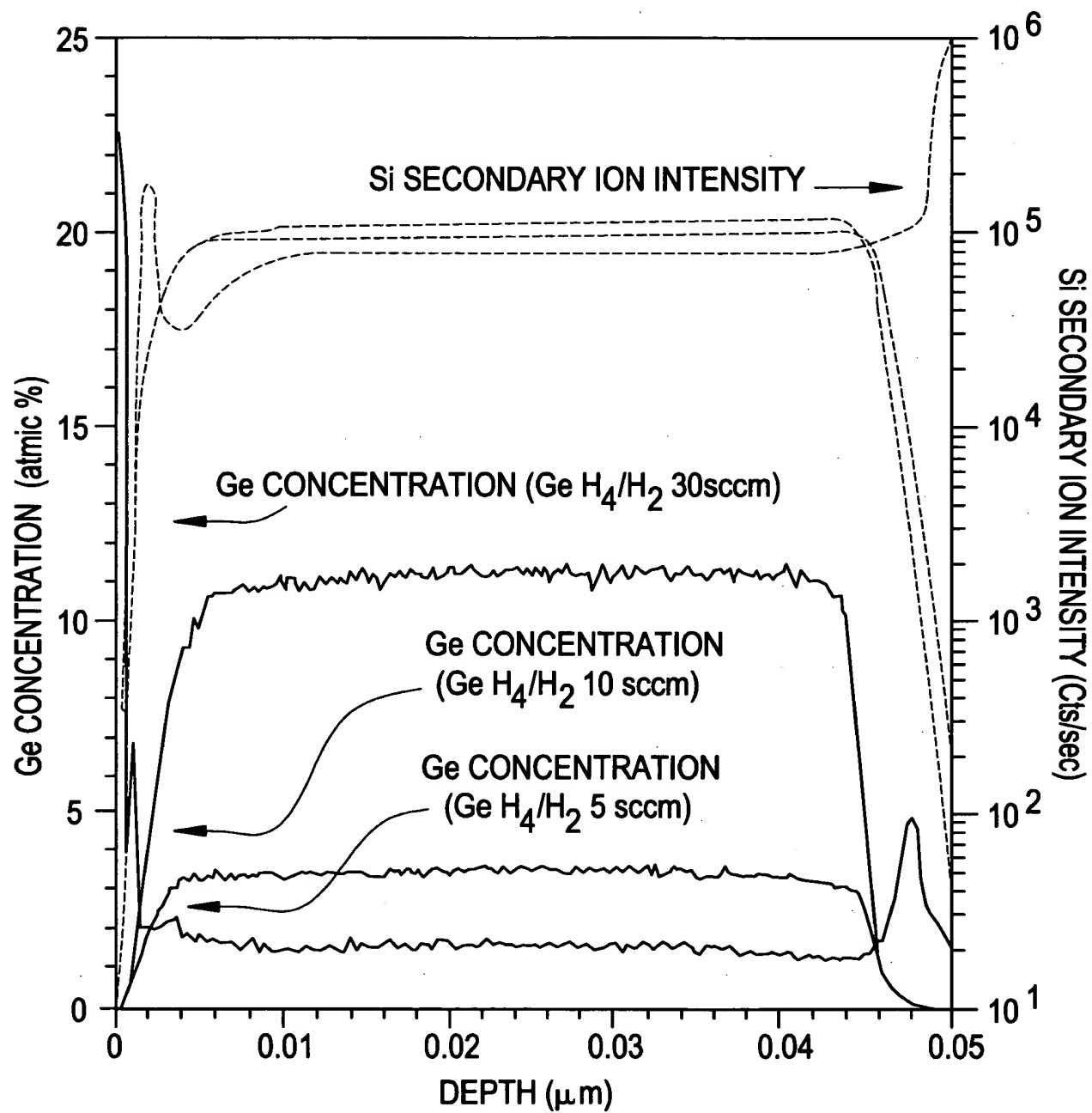
FIG. 2





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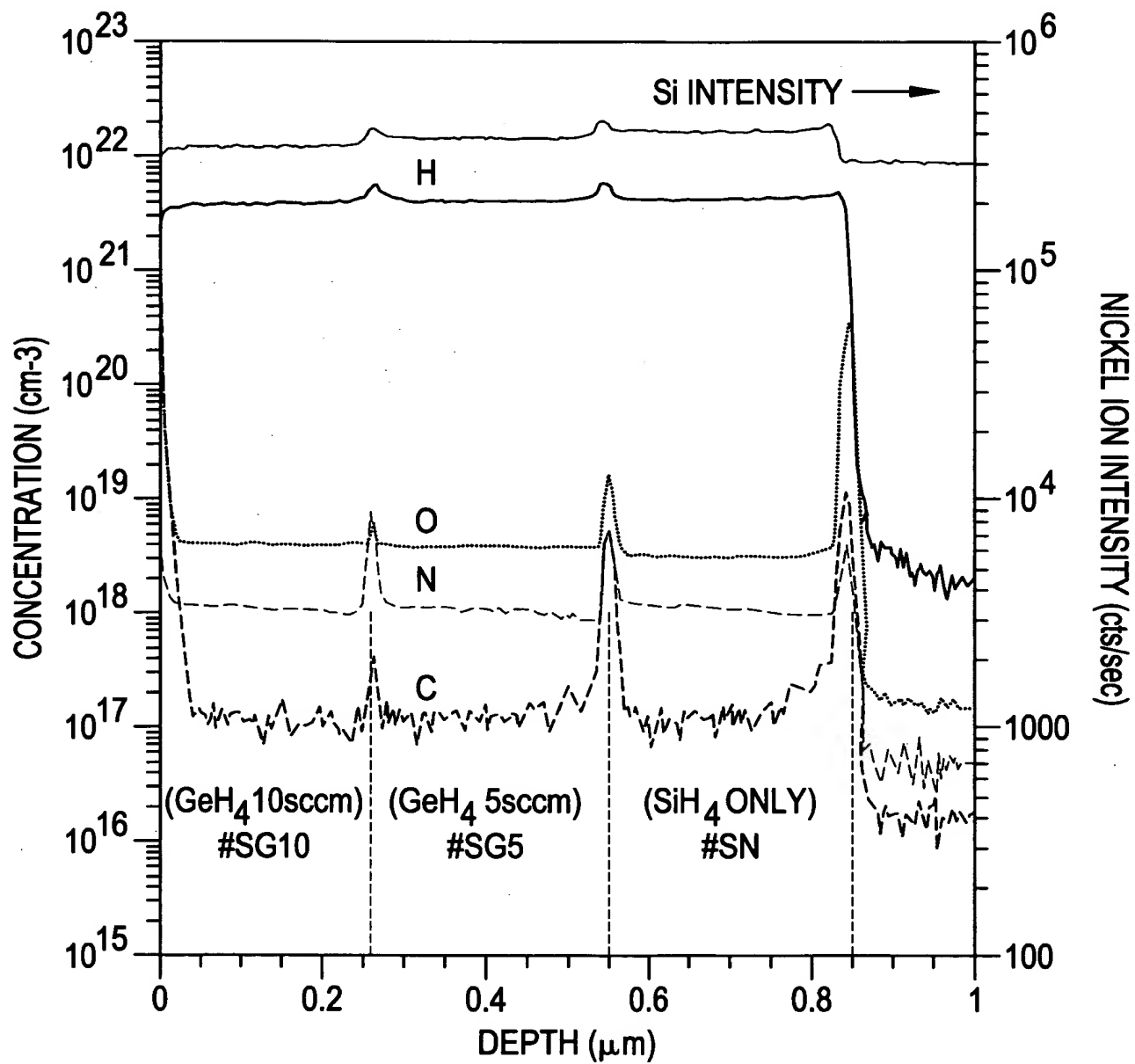
FIG. 3

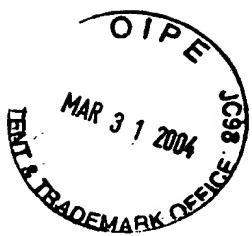




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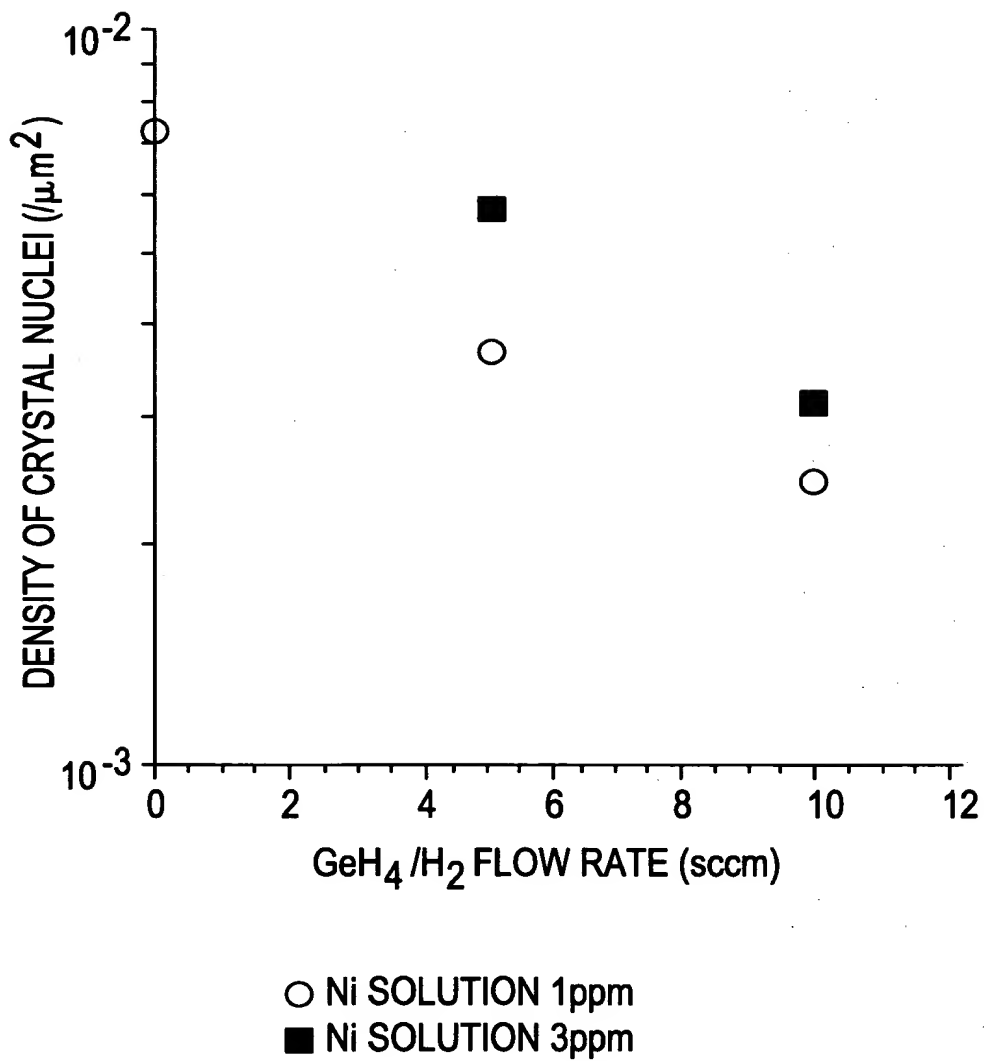
FIG. 4





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FIG. 5





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FIG. 6

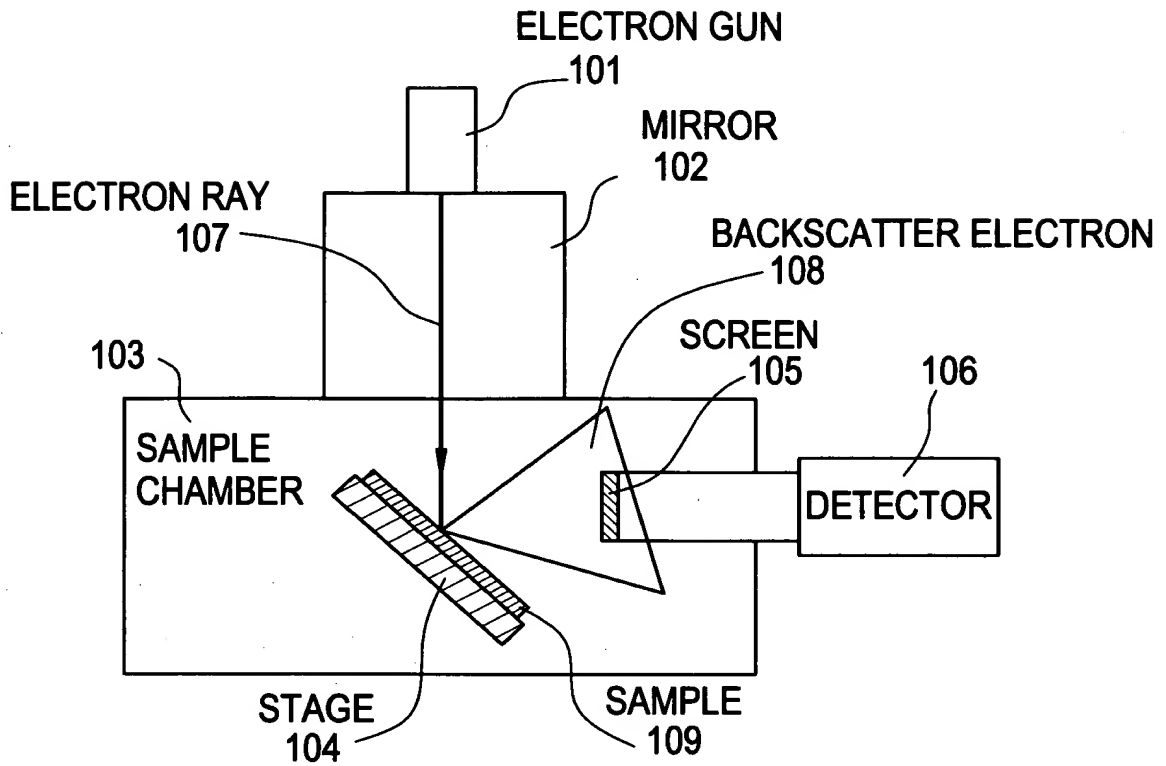
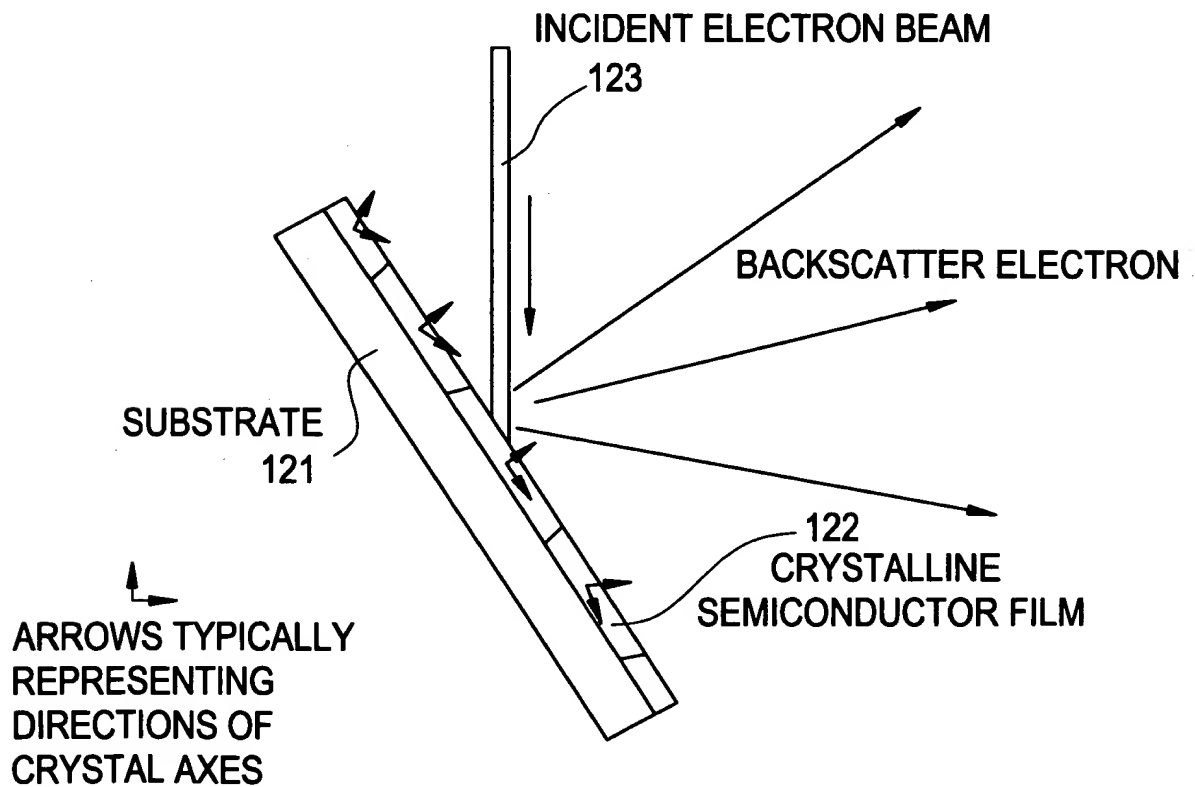
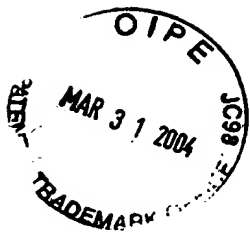


FIG. 7





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FIG. 8A

PLOTS OF ALL OF MEASUREMENT POINTS
IN MAPPING MEASUREMENT

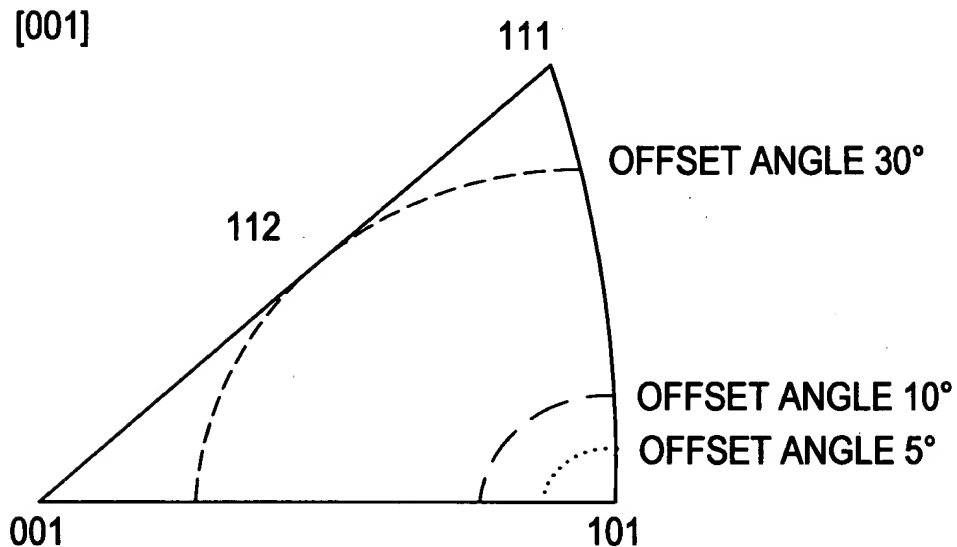
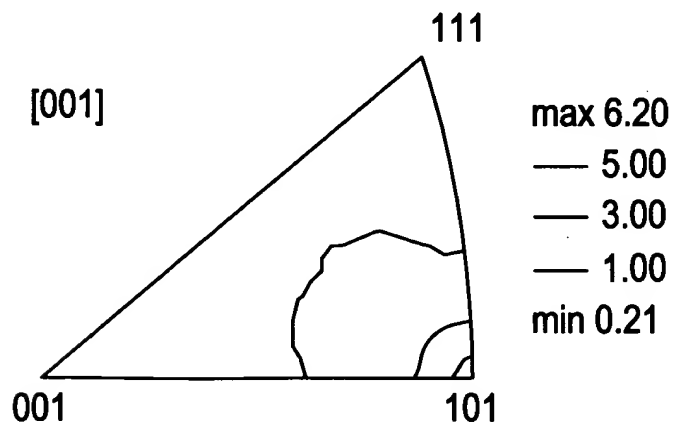


FIG. 8B

EXAMPLE OF TRANSLATING CONCENTRATION OF POINTS
OF FIG. 8A INTO CONTOUR



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FIG. 9

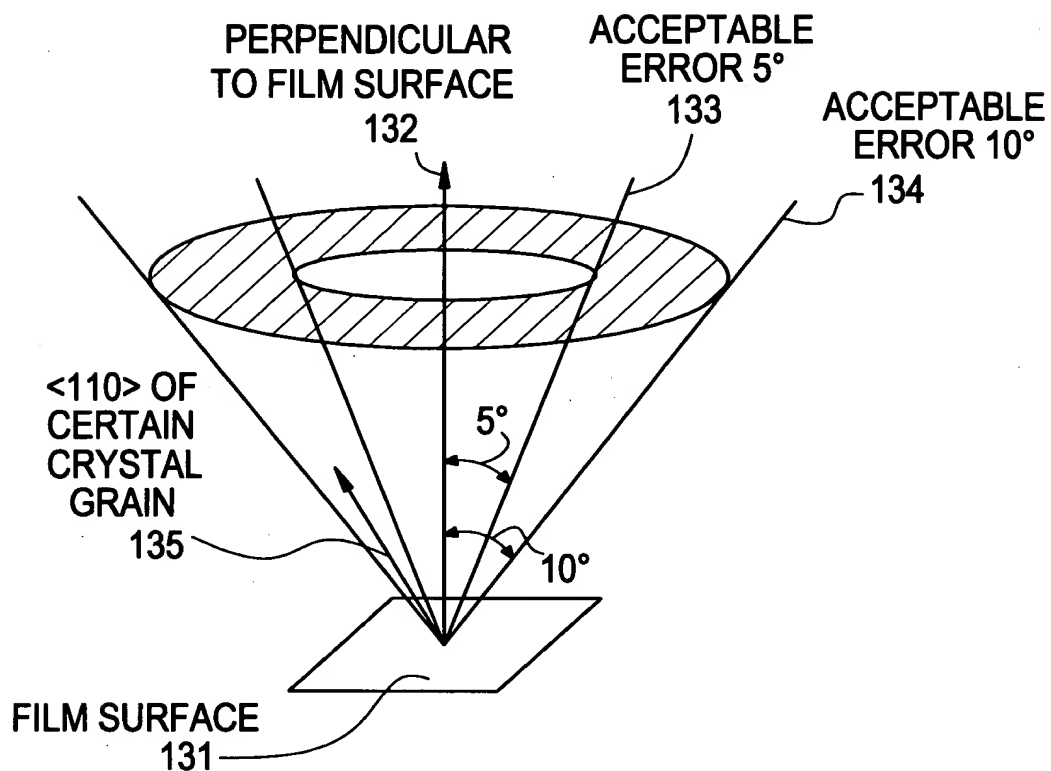
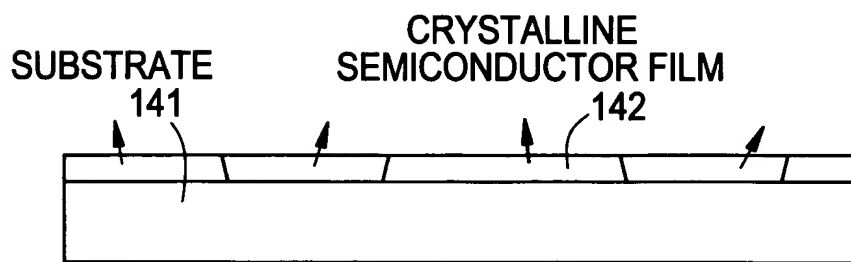


FIG. 10



VIEW EXPLAINING FLUCTUATION OF <101> ORIENTATION
OF CRYSTAL GRAIN



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FIG. 11A

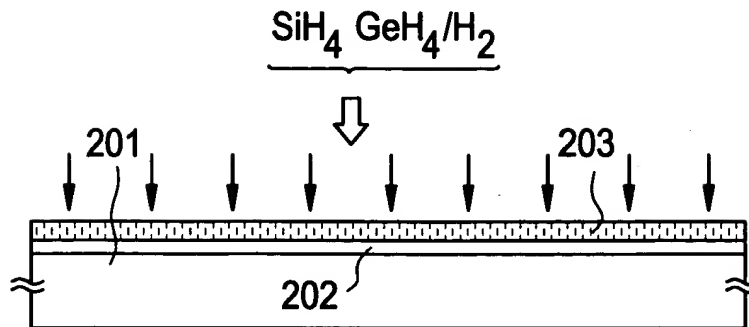


FIG. 11B

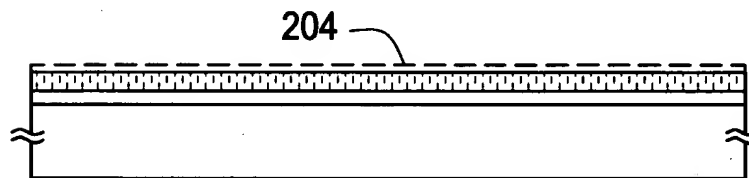


FIG. 11C

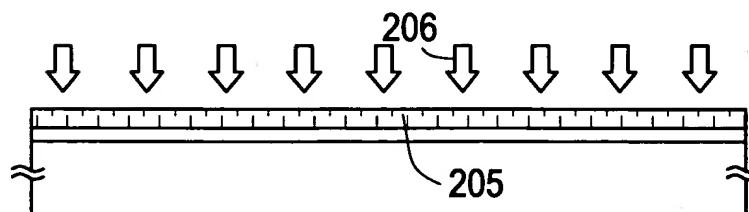
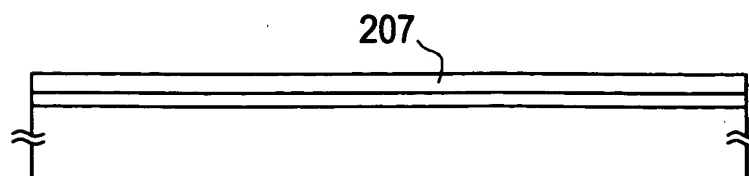


FIG. 11D



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FIG. 12A

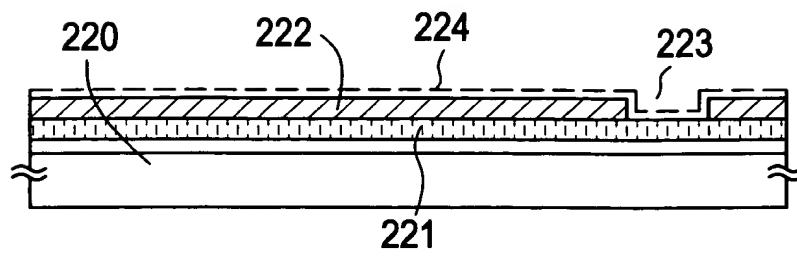


FIG. 12B

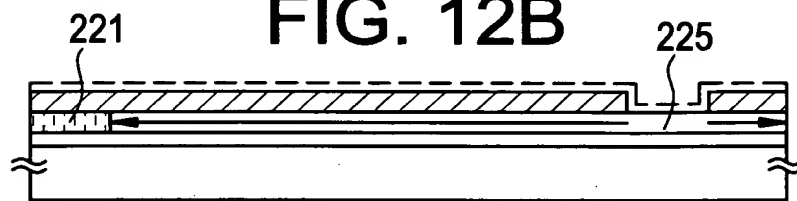


FIG. 12C

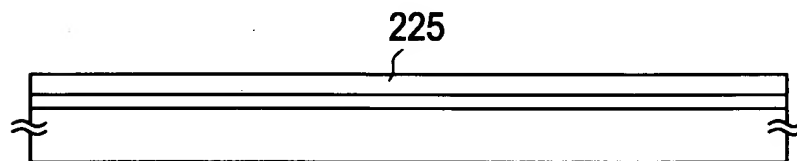


FIG. 13A

P ION IMPLANTATION

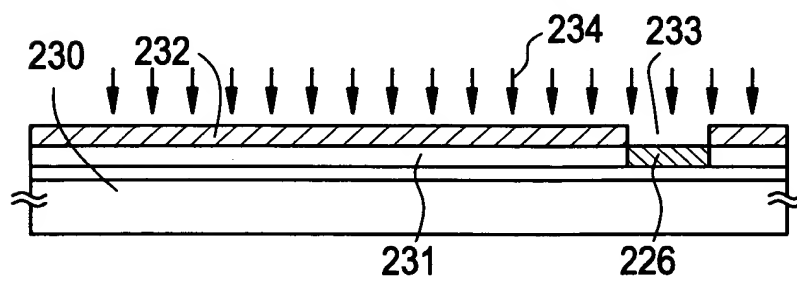


FIG. 13B

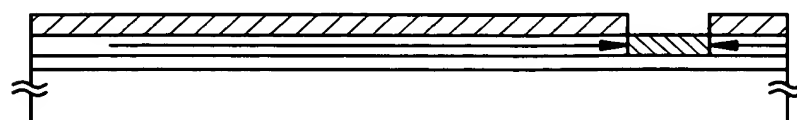
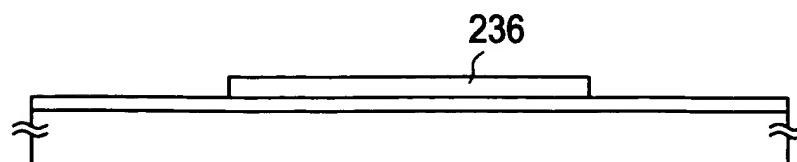


FIG. 13C



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FIG. 14A

B DOPING

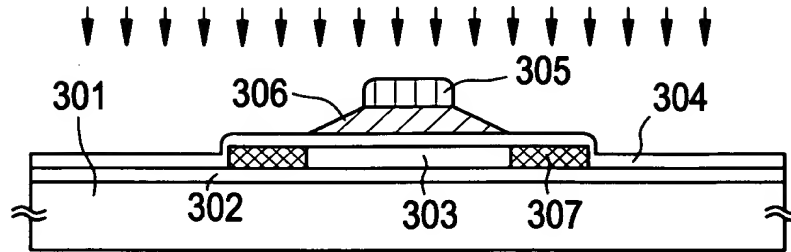


FIG. 14B

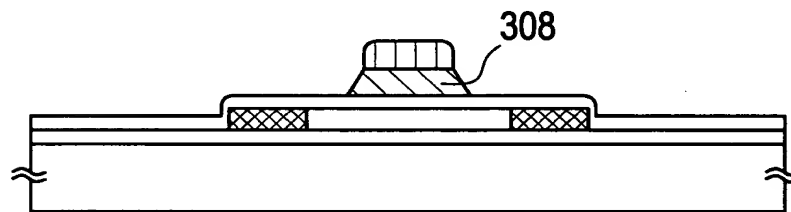


FIG. 14C

B DOPING

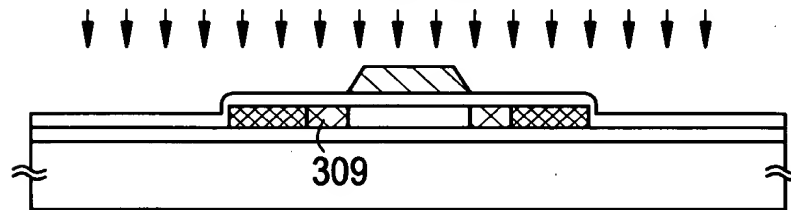
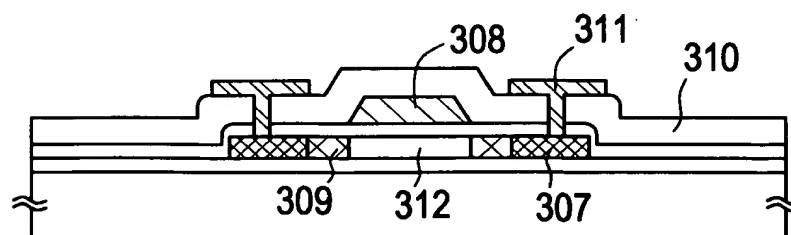


FIG. 14D



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FIG. 15A

P DOPING

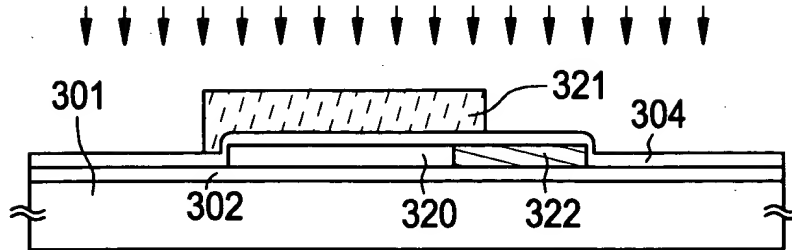


FIG. 15B

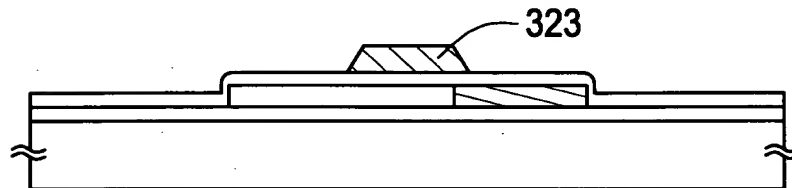


FIG. 15C

P DOPING

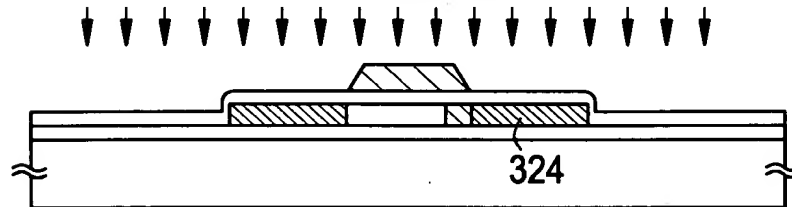


FIG. 15D

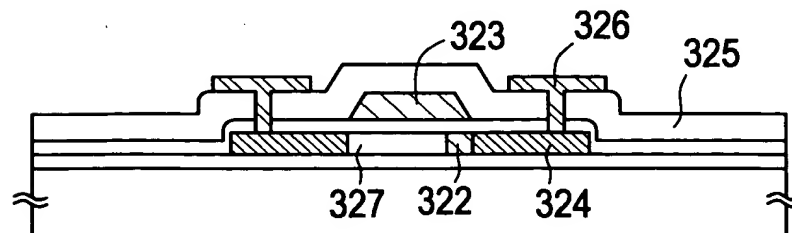


FIG. 16A

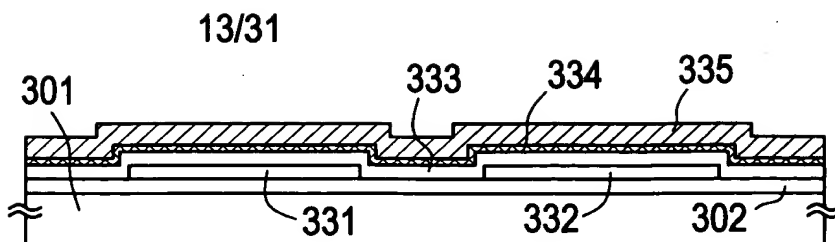


FIG. 16B

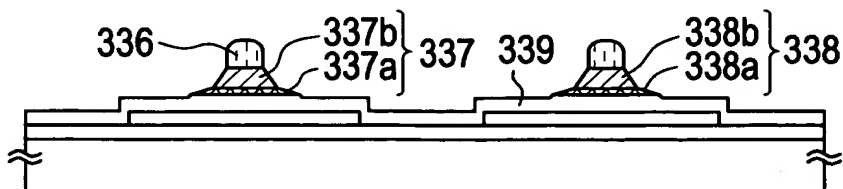


FIG. 16C

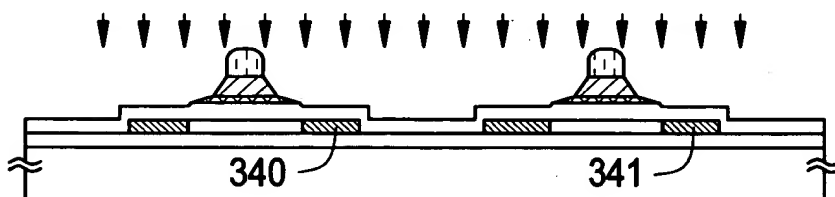


FIG. 16D

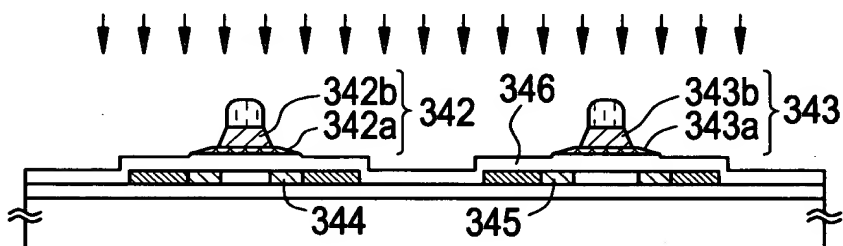


FIG. 16E

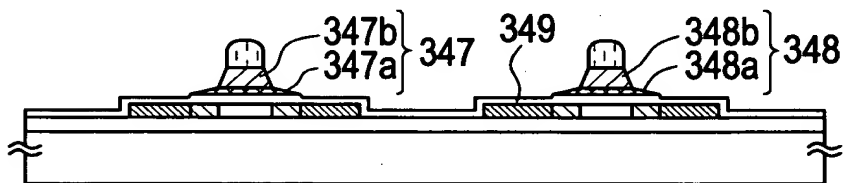


FIG. 16F

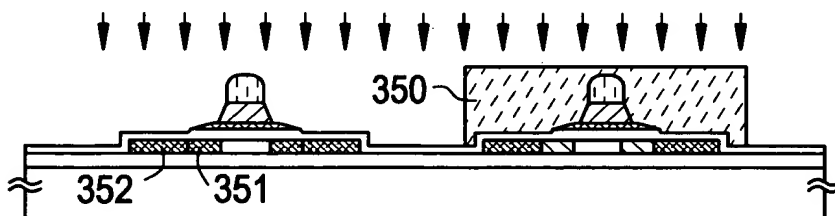


FIG. 16G

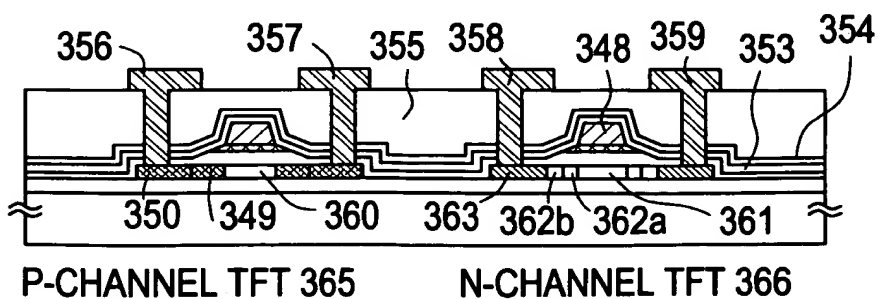
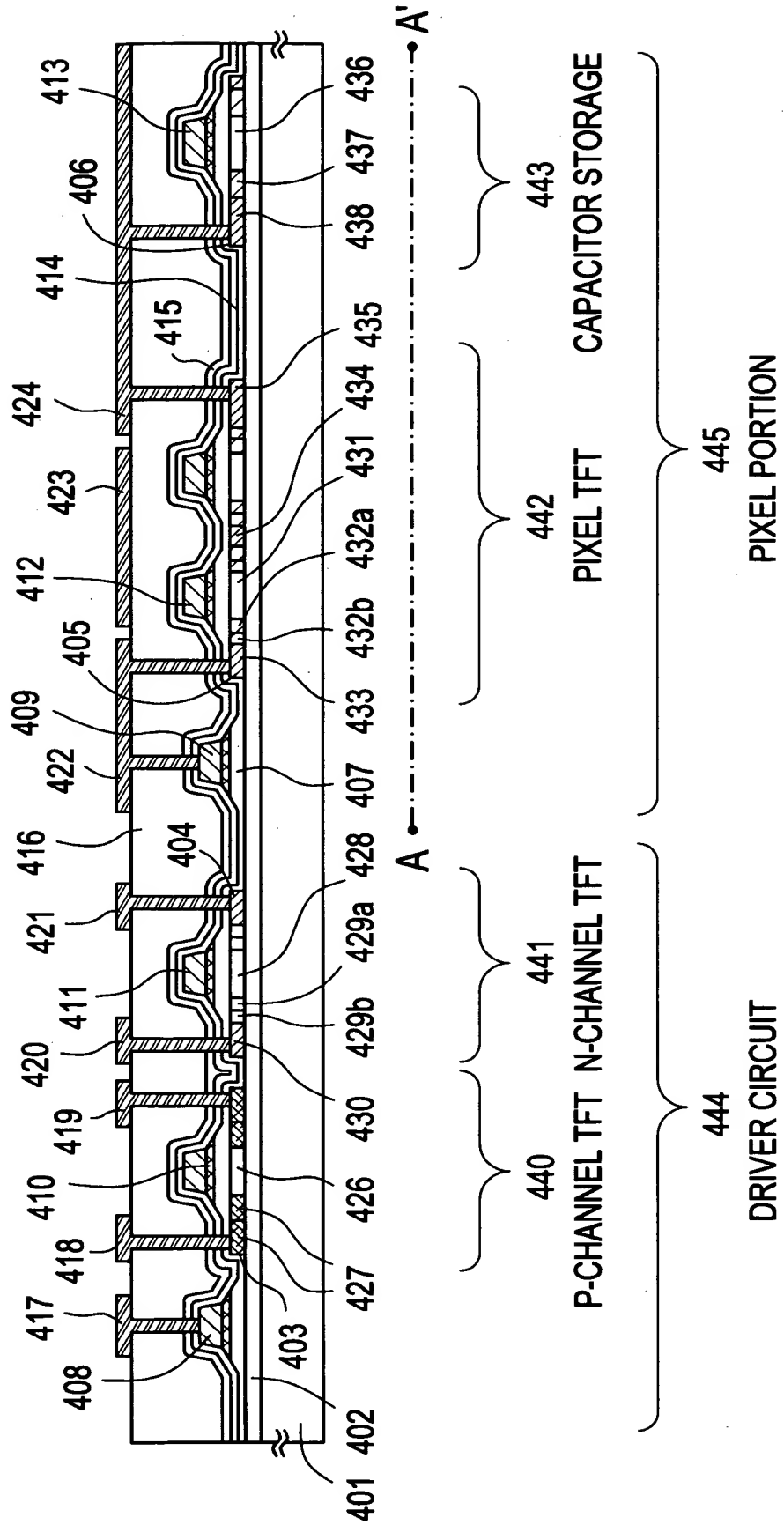


FIG. 17



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FIG. 18

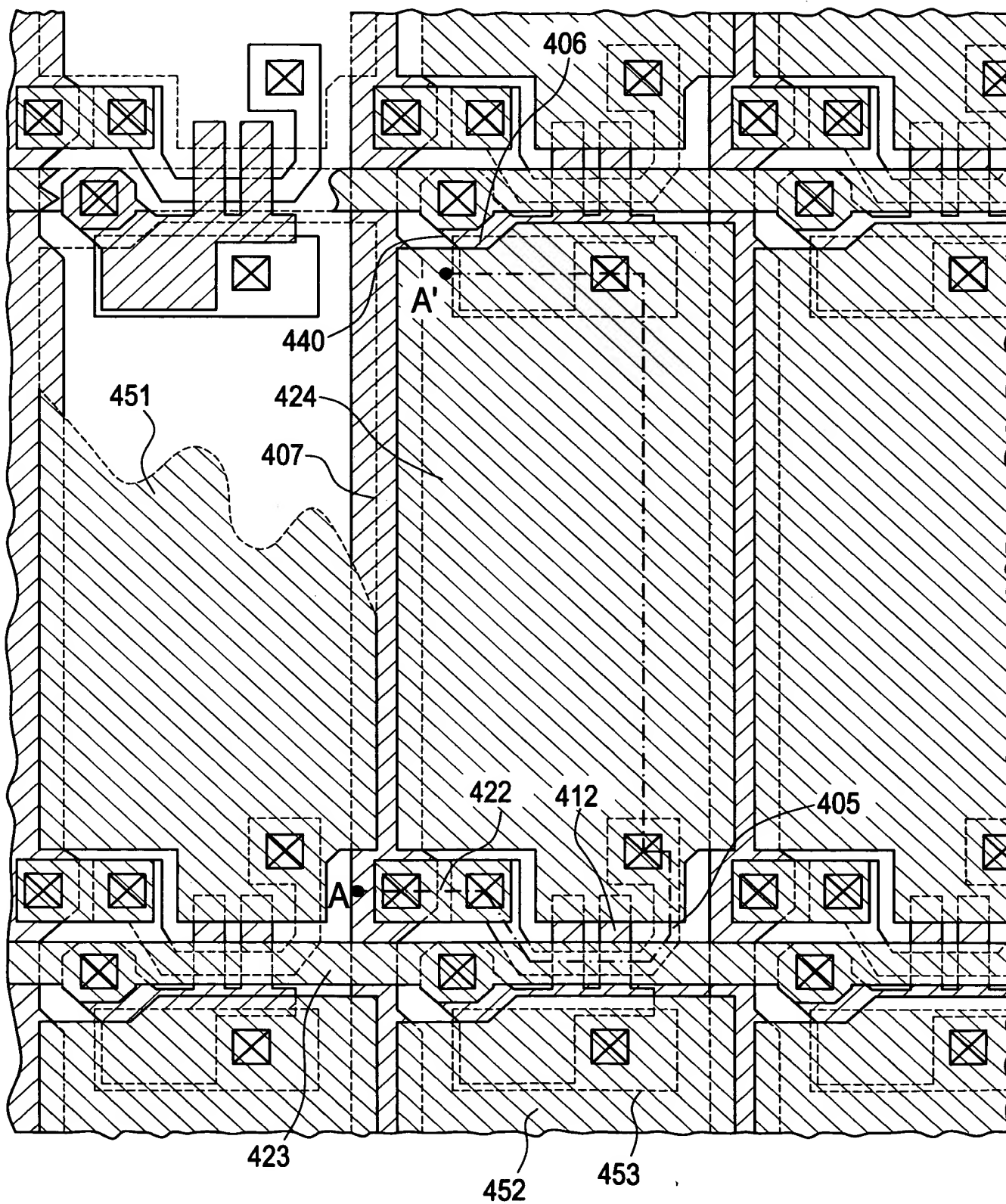
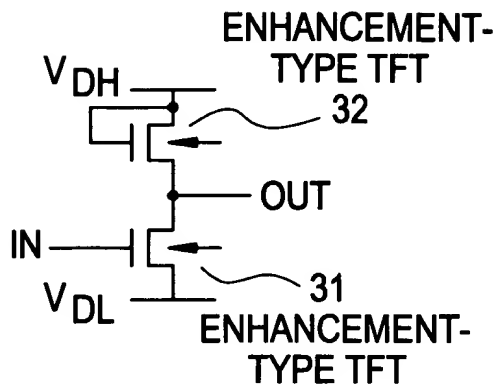


FIG. 19A

EEMOS CIRCUIT

**FIG. 19B**

EDMOS CIRCUIT

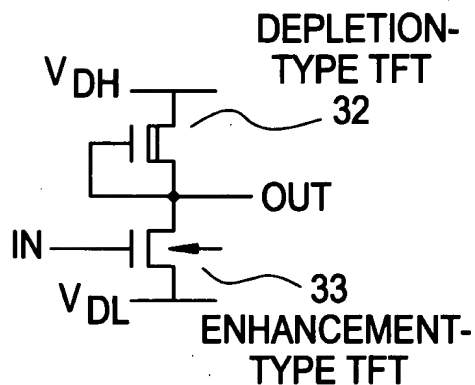
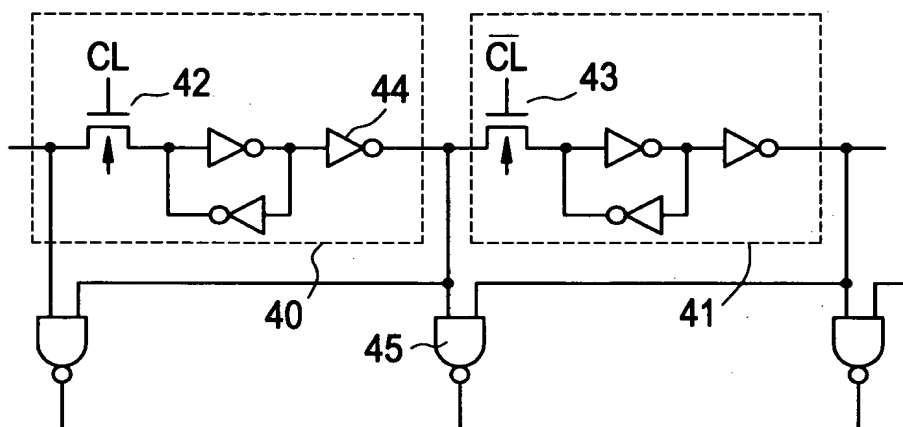
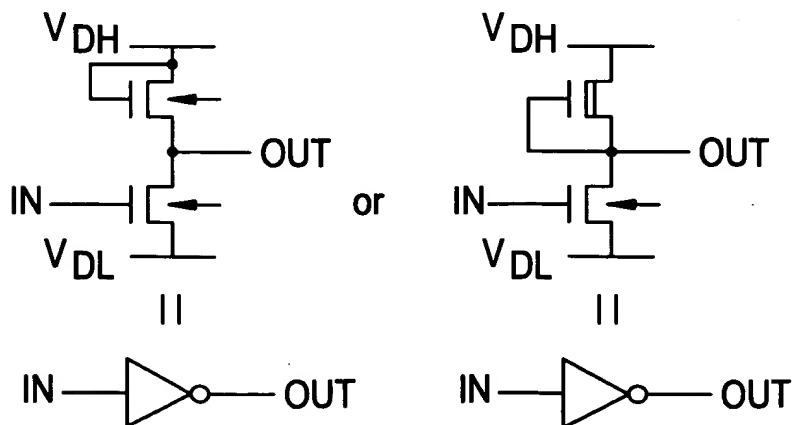
**FIG. 20A****FIG. 20B**

FIG. 21

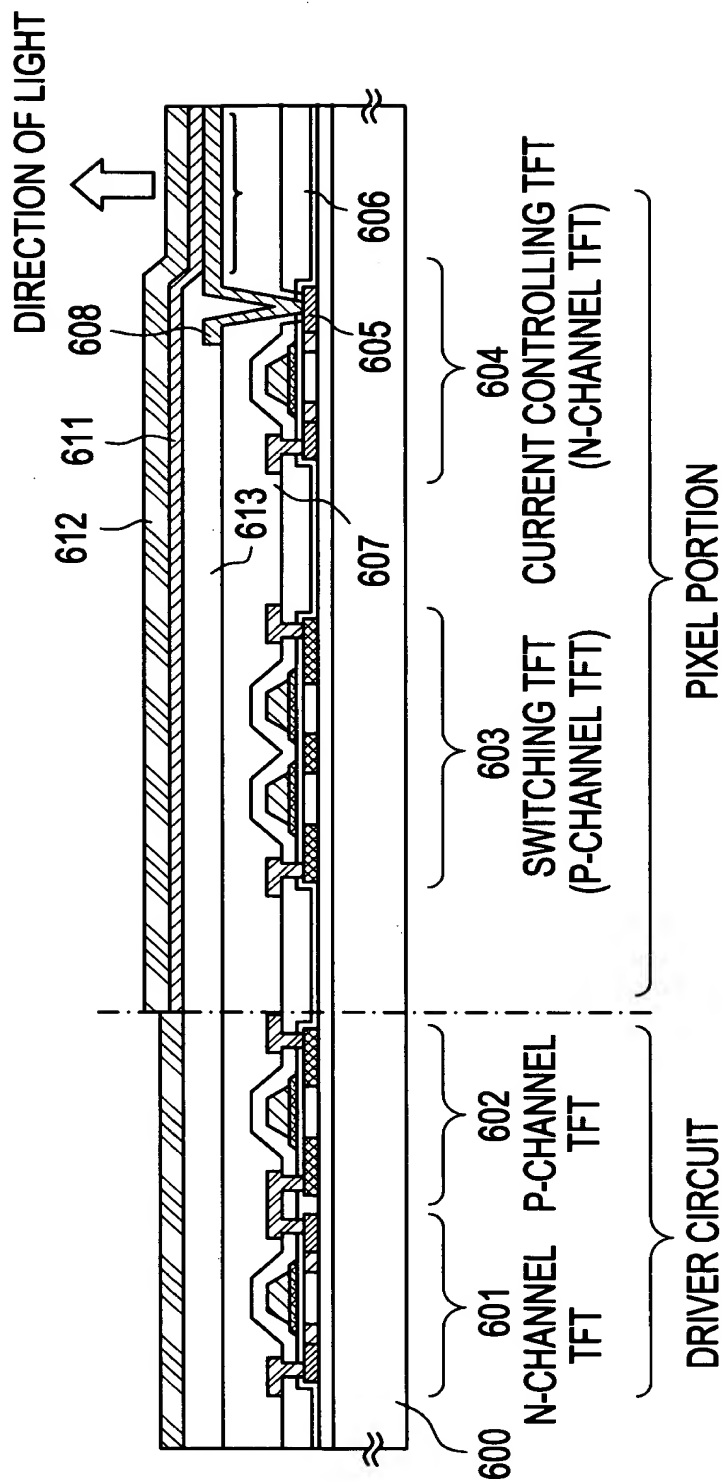




FIG. 22A

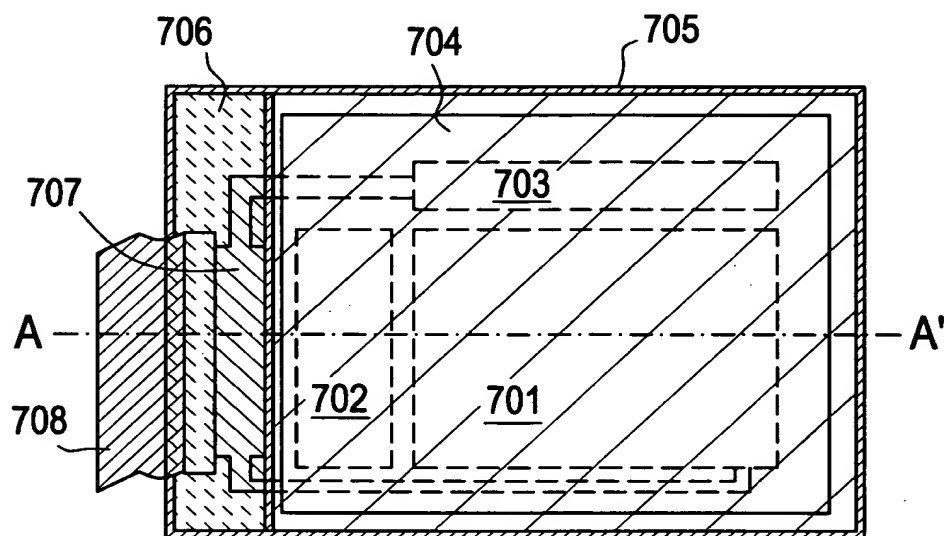
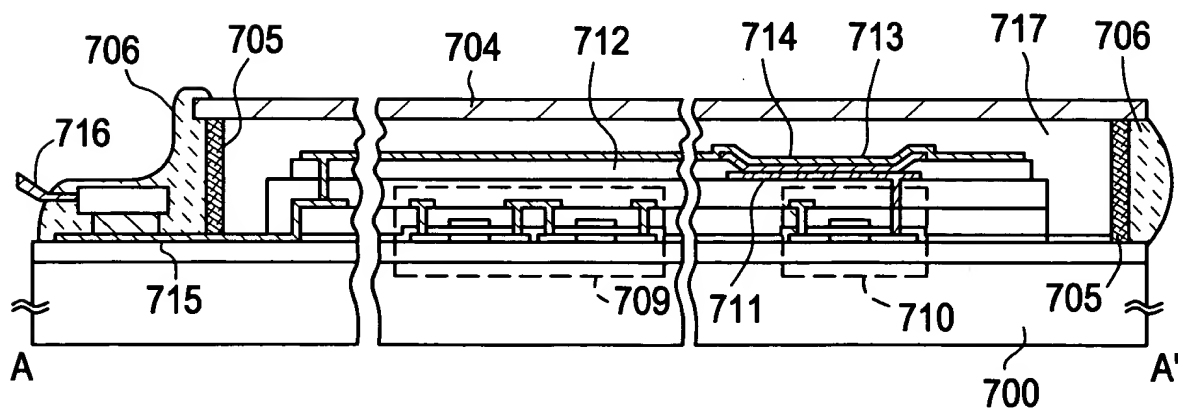


FIG. 22B





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FIG. 23A

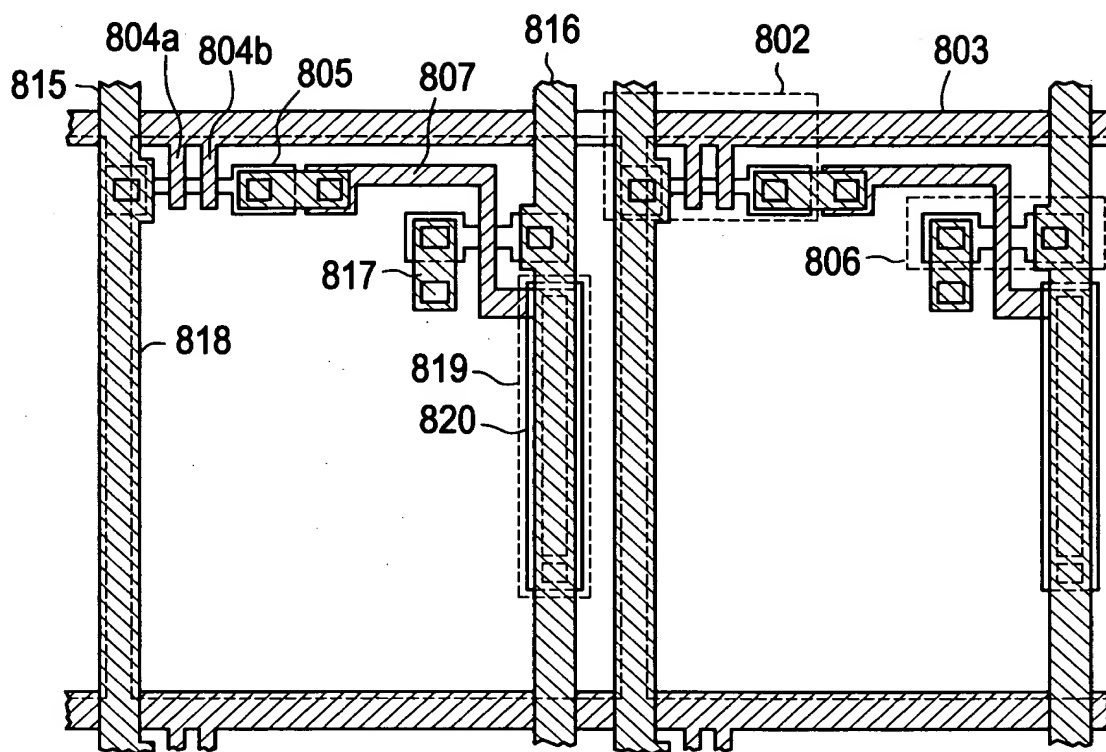


FIG. 23B

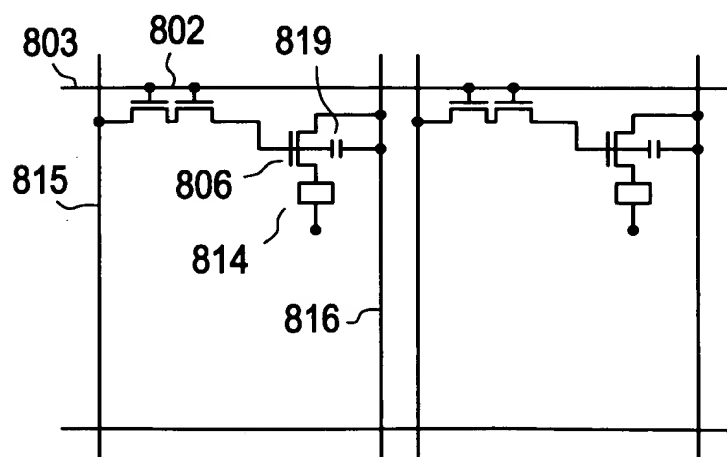




FIG. 24

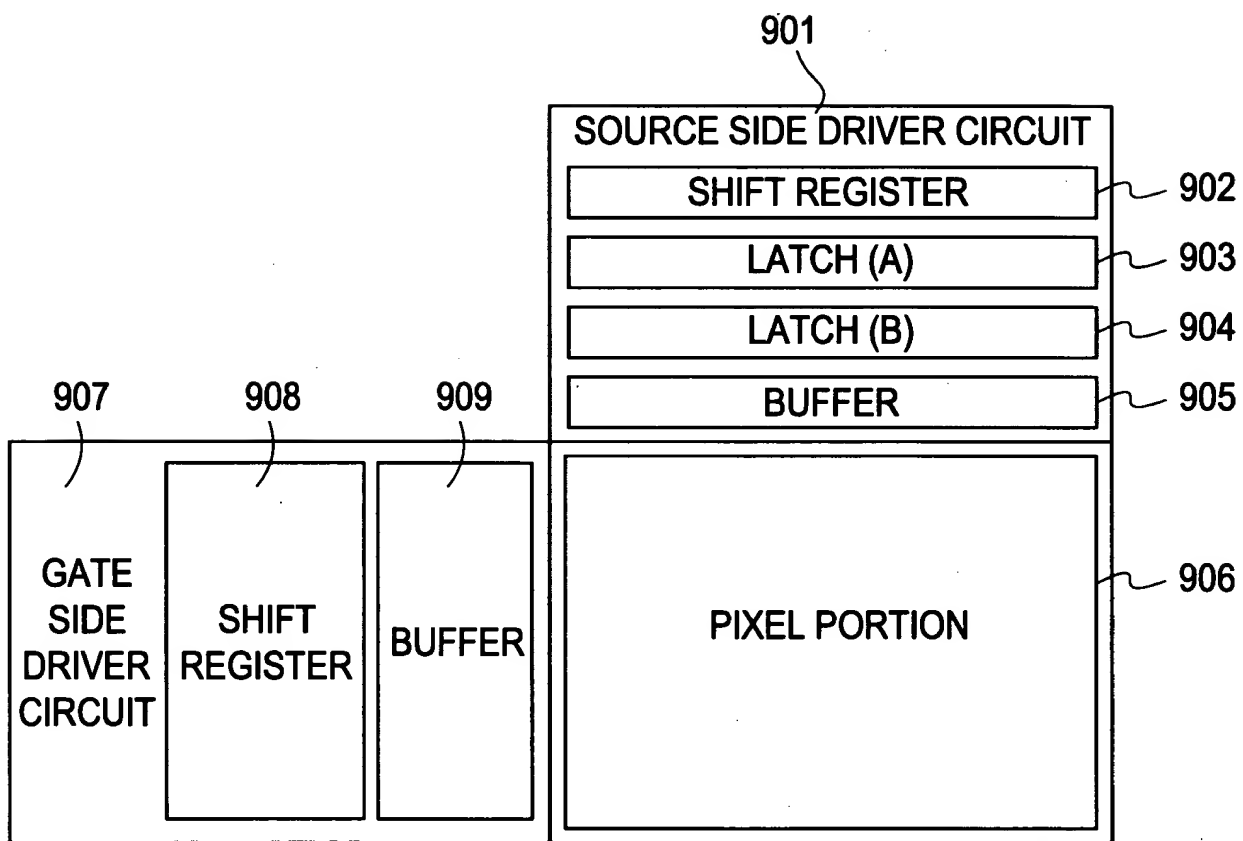


FIG. 25

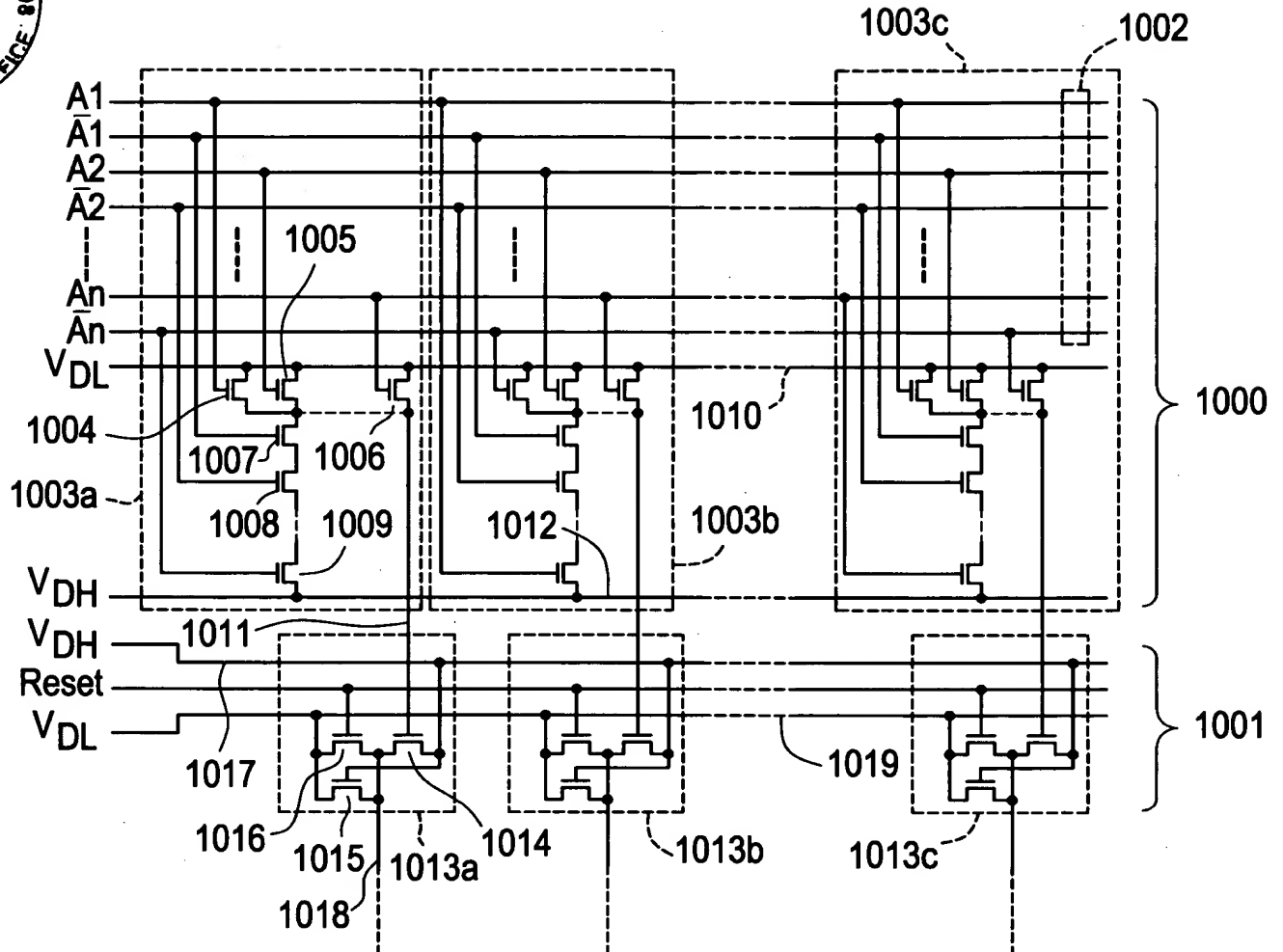


FIG. 26

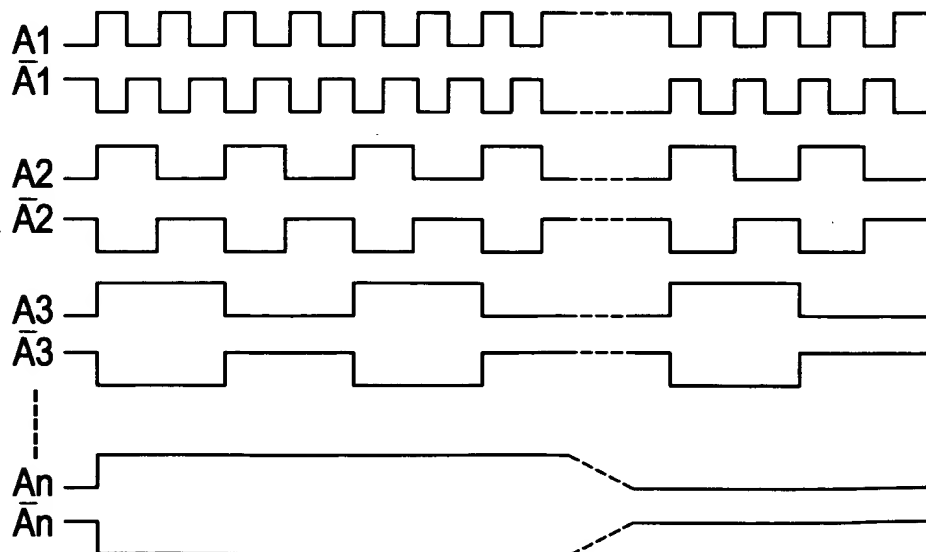
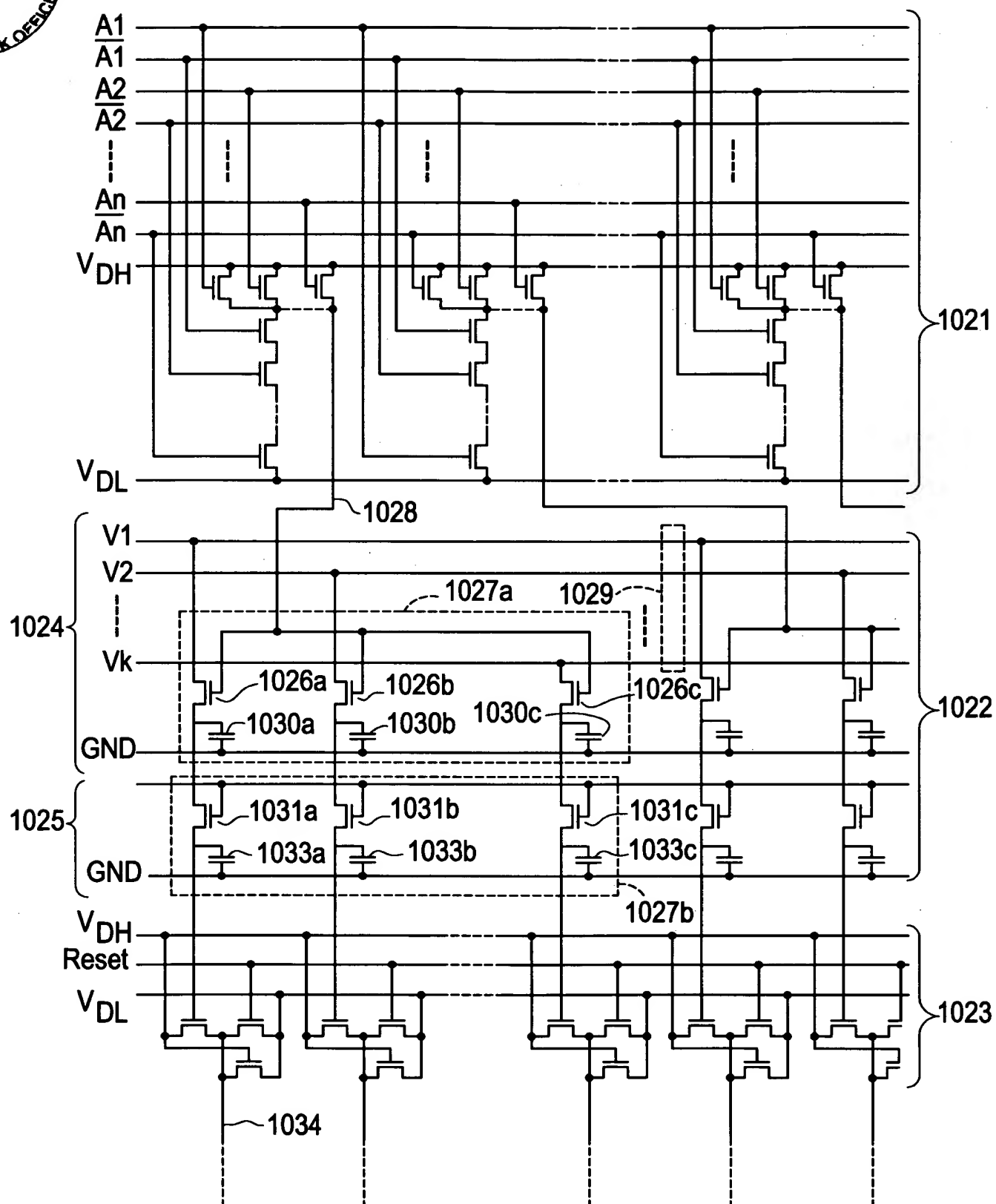


FIG. 27





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FIG. 28

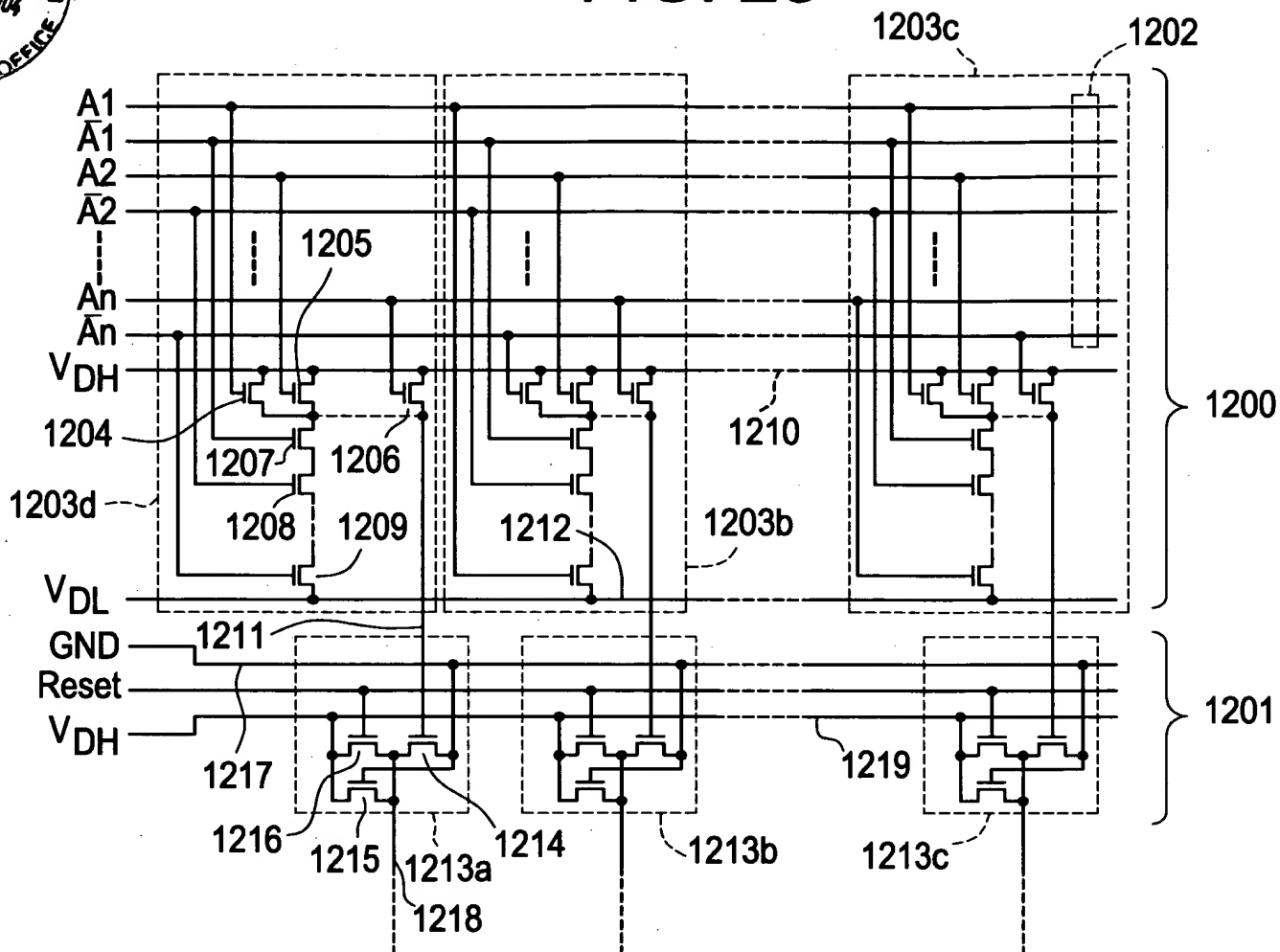
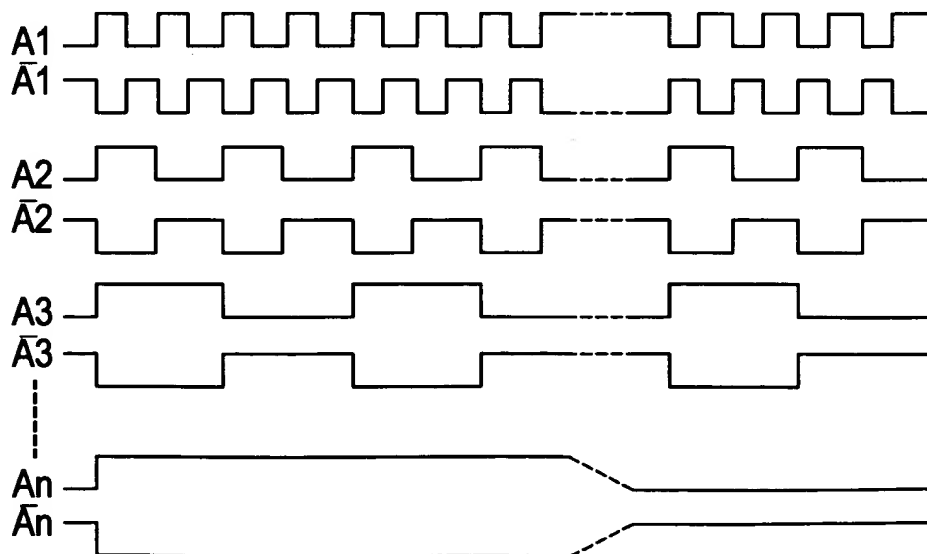


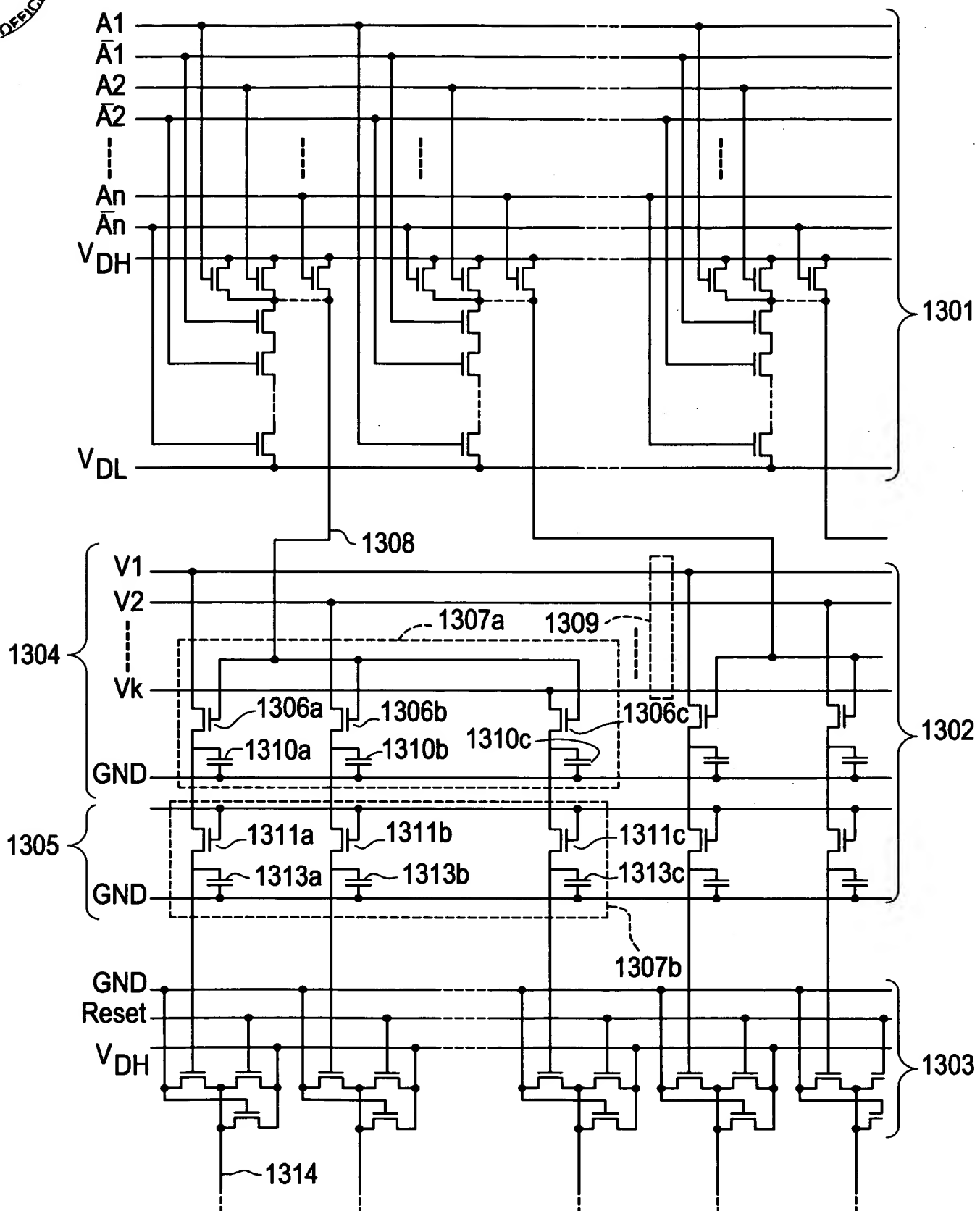
FIG. 29





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FIG. 30





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FIG. 31A

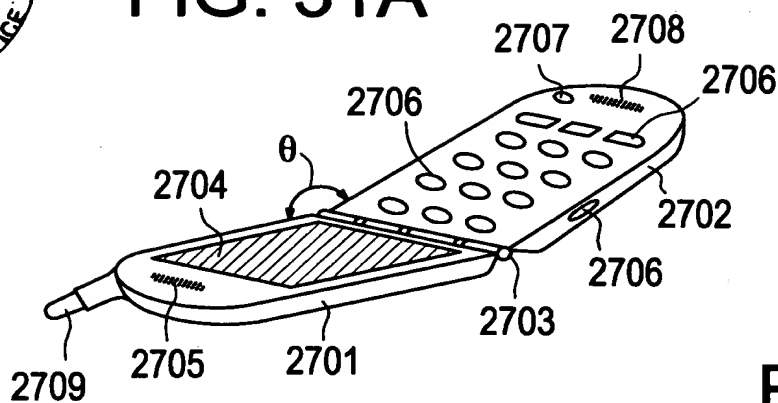


FIG. 31B

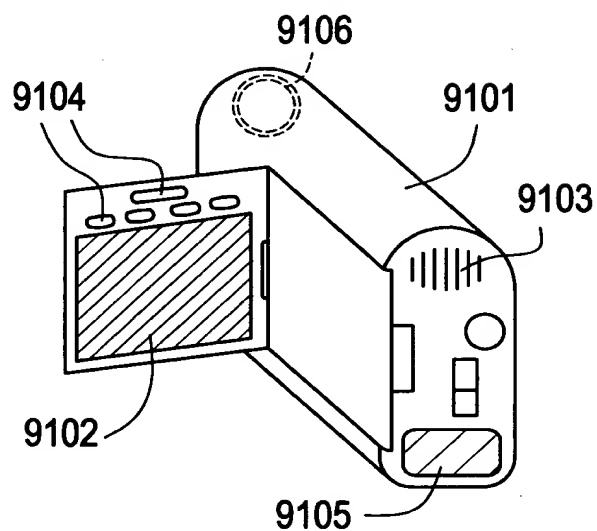


FIG. 31C

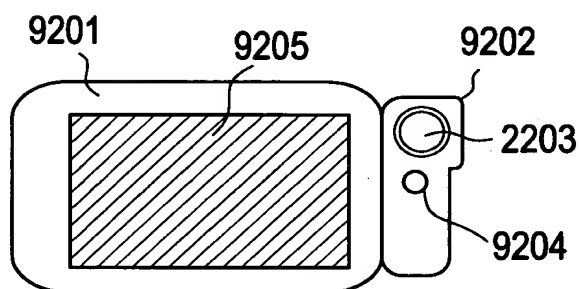


FIG. 31D

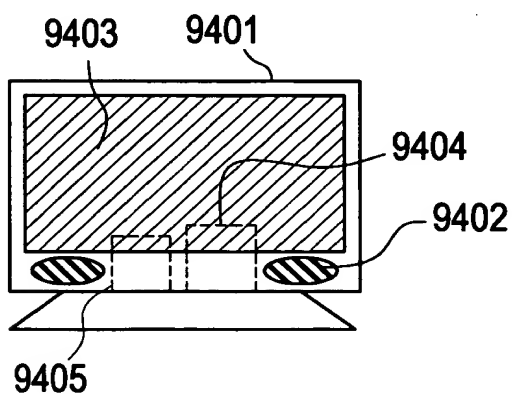
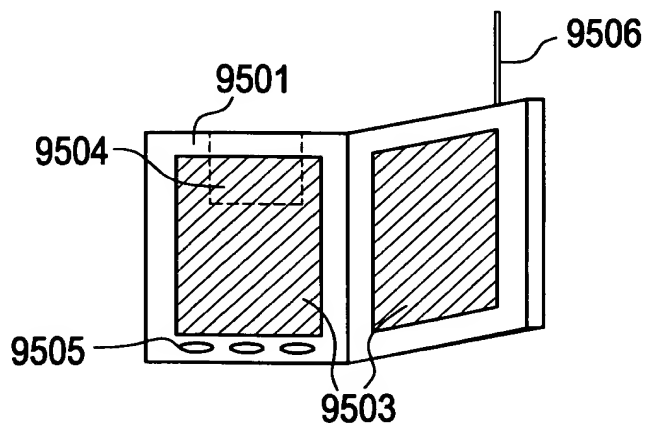


FIG. 31E



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FIG. 32A

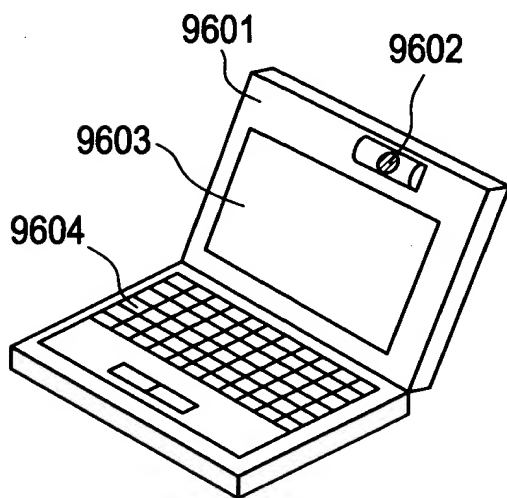


FIG. 32B

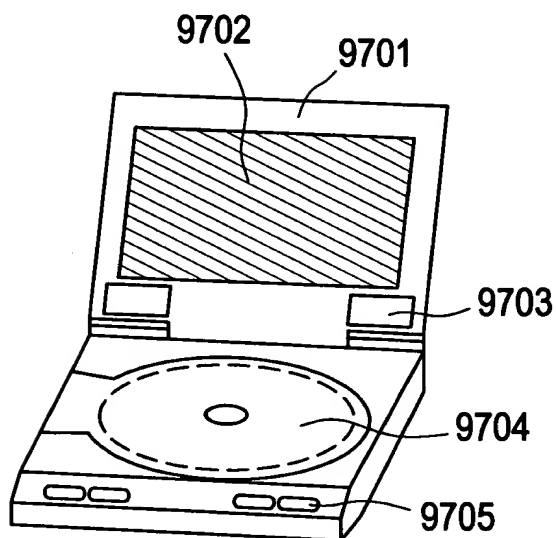
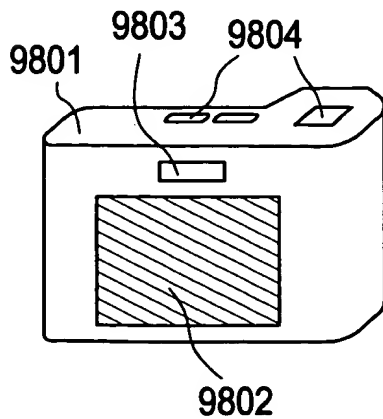


FIG. 32C





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FIG. 33A

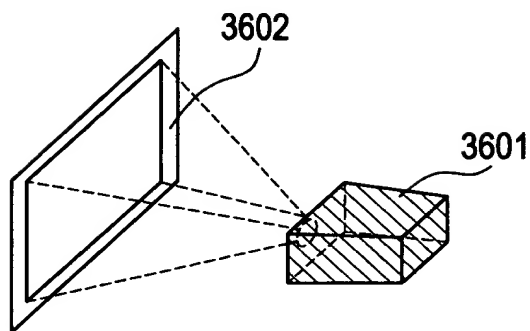


FIG. 33B

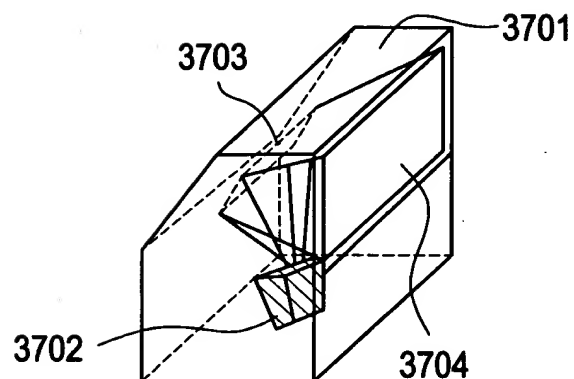


FIG. 33C

PROJECTING APPATUS (THREE PLATE TYPE)

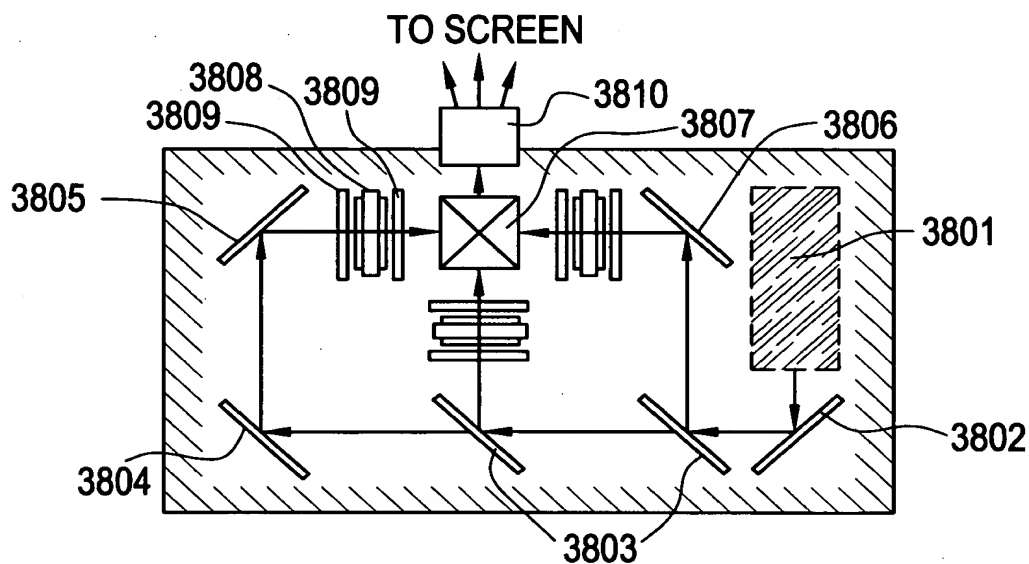
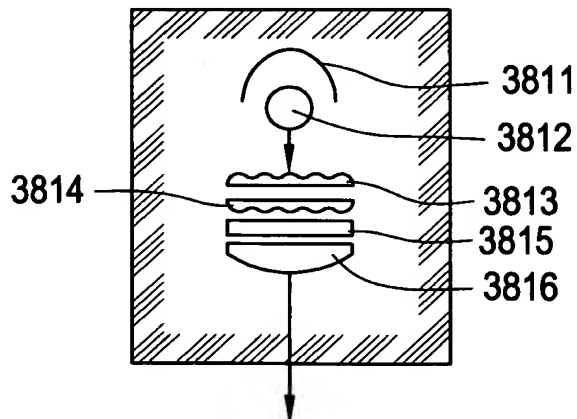


FIG. 33D

LIGHT SOURCE OPTICAL SYSTEM





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FIG. 34

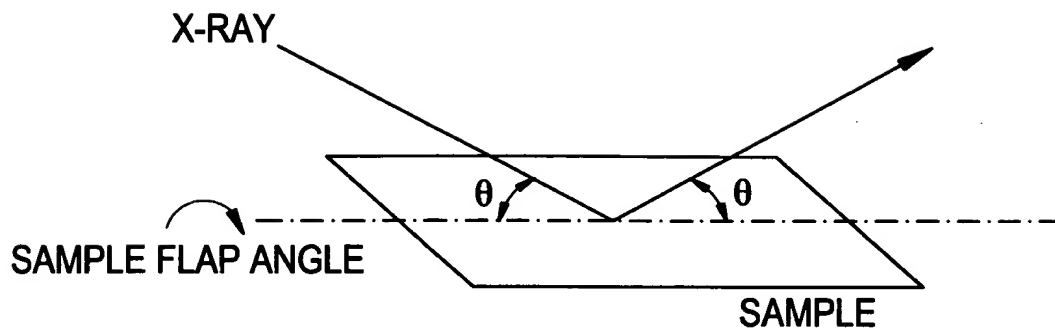


FIG. 35A

IN CASE OF FLAP ANGLE 0°

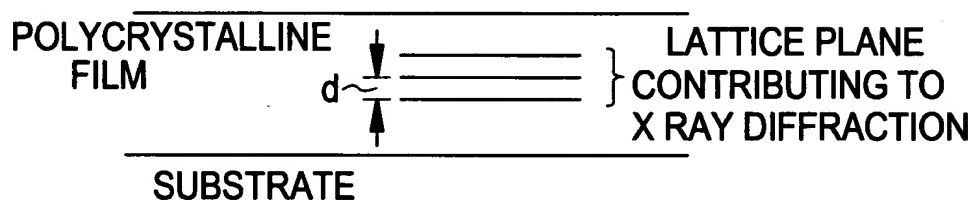


FIG. 35B

IN CASE OF FLAP ANGLE 60°

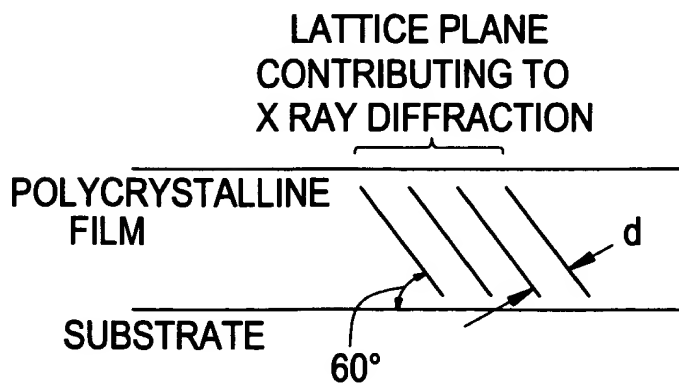
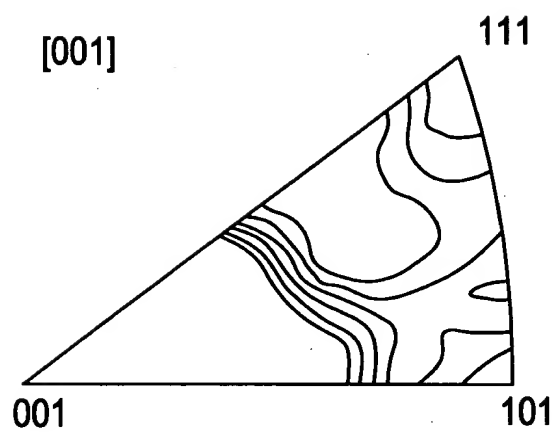




FIG. 36





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FIG. 37A
CRYSTALLIZATION

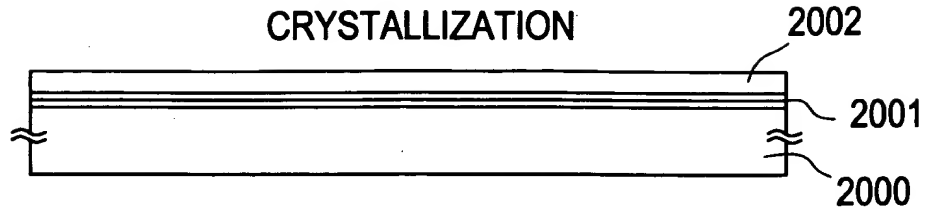


FIG. 37B

FORMATION OF BARRIER LAYER AND
FORMATION OF SEMICONDUCTOR FILM



FIG. 37C

DOPING WITH NOBLE GAS

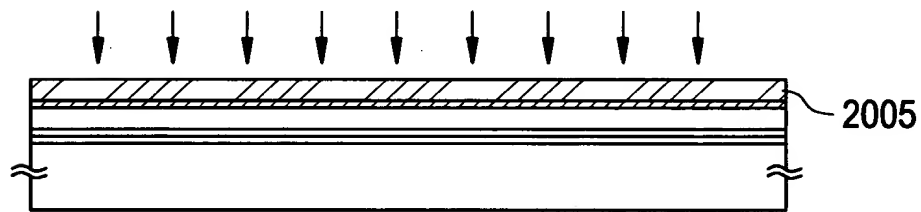


FIG. 37D

GETTERING

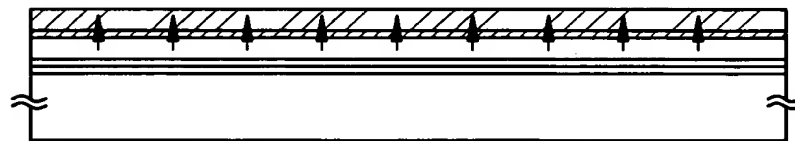
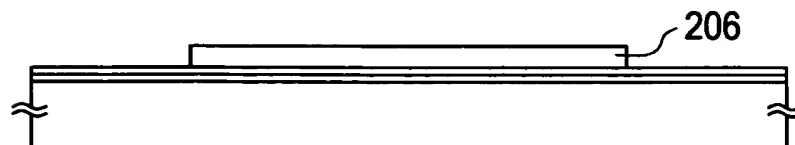


FIG. 37E

FORMATION OF SEMICONDUCTOR ISLAND





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FIG. 38

